

# MUN2112, MMUN2112L, MUN5112, DTA124EE, DTA124EM3, NSBA124EF3

## Digital Transistors (BRT) R1 = 22 kΩ, R2 = 22 kΩ

### PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

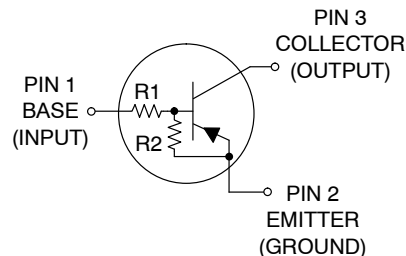
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



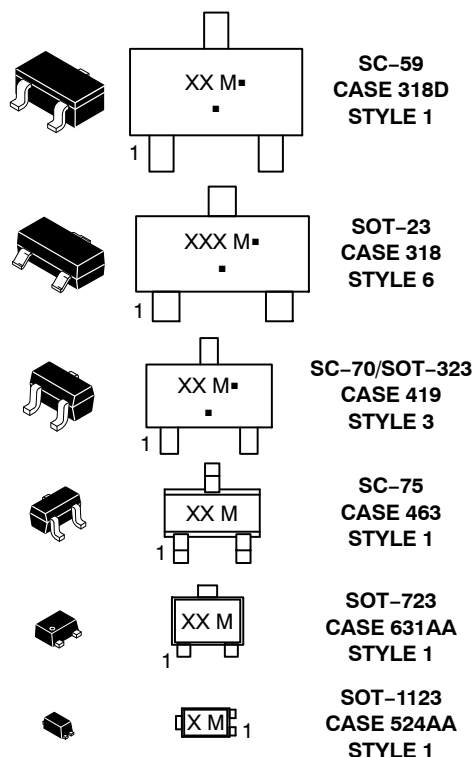
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

#### PIN CONNECTIONS



#### MARKING DIAGRAMS



XXX = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

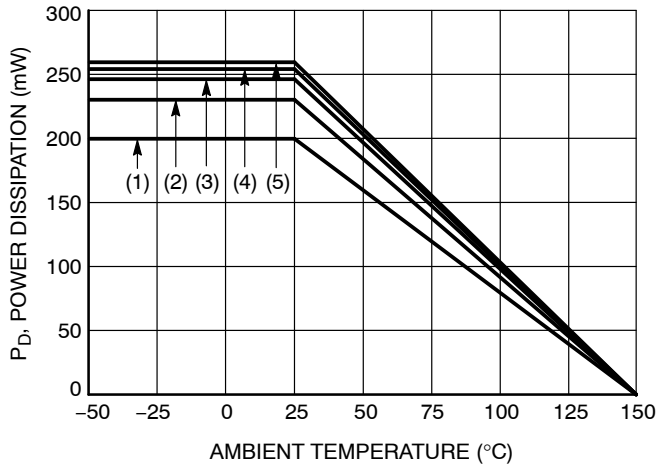
See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

# MUN2112, MMUN2112L, MUN5112, DTA124EE, DTA124EM3, NSBA124EF3

**Table 1. ORDERING INFORMATION**

Device	Part Marking	Package	Shipping†
MUN2112T1G, NSVMUN2112T1G	6B	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2112LT1G, NSVMMUN2112LT1G	A6B	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5112T1G, SMUN5112T1G	6B	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA124EET1G	6B	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA124EM3T5G	6B	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBA124EF3T5G	Y	SOT-1123 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

**Figure 1. Derating Curve**

# MUN2112, MMUN2112L, MUN5112, DTA124EE, DTA124EM3, NSBA124EF3

**Table 2. THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
<b>THERMAL CHARACTERISTICS (SC-59) (MUN2112)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) (Note 2) Derate above $25^\circ\text{C}$ (Note 1) (Note 2)	$P_D$	230 338 1.8 2.7	mW  mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	540 370	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead (Note 1) (Note 2)	$R_{\theta JL}$	264 287	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SOT-23) (MMUN2112L)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) (Note 2) Derate above $25^\circ\text{C}$ (Note 1) (Note 2)	$P_D$	246 400 2.0 3.2	mW  mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	508 311	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead (Note 1) (Note 2)	$R_{\theta JL}$	174 208	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5112)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) (Note 2) Derate above $25^\circ\text{C}$ (Note 1) (Note 2)	$P_D$	202 310 1.6 2.5	mW  mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	618 403	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead (Note 1) (Note 2)	$R_{\theta JL}$	280 332	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SC-75) (DTA124EE)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) (Note 2) Derate above $25^\circ\text{C}$ (Note 1) (Note 2)	$P_D$	200 300 1.6 2.4	mW  mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	600 400	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SOT-723) (DTA124EM3)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) (Note 2) Derate above $25^\circ\text{C}$ (Note 1) (Note 2)	$P_D$	260 600 2.0 4.8	mW  mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	480 205	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
- FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

MUN2112, MMUN2112L, MUN5112, DTA124EE, DTA124EM3, NSBA124EF3

**Table 2. THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
<b>THERMAL CHARACTERISTICS (SOT-1123) (NSBA124EF3)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 3) (Note 4) Derate above $25^\circ\text{C}$ (Note 3) (Note 4)	$P_D$	254 297 2.0 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 3) (Note 4)	$R_{\theta JA}$	493 421	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead (Note 3)	$R_{\theta JL}$	193	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
- FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 3. ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Base Cutoff Current ( $V_{CB} = 50\text{ V}, I_E = 0$ )	$I_{CBO}$	-	-	100	nAdc
Collector-Emitter Cutoff Current ( $V_{CE} = 50\text{ V}, I_B = 0$ )	$I_{CEO}$	-	-	500	nAdc
Emitter-Base Cutoff Current ( $V_{EB} = 6.0\text{ V}, I_C = 0$ )	$I_{EBO}$	-	-	0.2	mAdc
Collector-Base Breakdown Voltage ( $I_C = 10\ \mu\text{A}, I_E = 0$ )	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 5) ( $I_C = 2.0\text{ mA}, I_B = 0$ )	$V_{(BR)CEO}$	50	-	-	Vdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain (Note 5) ( $I_C = 5.0\text{ mA}, V_{CE} = 10\text{ V}$ )	$h_{FE}$	60	100	-	
Collector-Emitter Saturation Voltage (Note 5) ( $I_C = 10\text{ mA}, I_B = 0.3\text{ mA}$ )	$V_{CE(sat)}$	-	-	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0\text{ V}, I_C = 100\ \mu\text{A}$ )	$V_{i(off)}$	-	1.2	0.8	Vdc
Input Voltage (on) ( $V_{CE} = 0.3\text{ V}, I_C = 5.0\text{ mA}$ )	$V_{i(on)}$	2.5	1.7	-	Vdc
Output Voltage (on) ( $V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$ )	$V_{OL}$	-	-	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0\text{ V}, V_B = 0.5\text{ V}, R_L = 1.0\text{ k}\Omega$ )	$V_{OH}$	4.9	-	-	Vdc
Input Resistor	R1	15.4	22	28.6	k $\Omega$
Resistor Ratio	$R_1/R_2$	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq$  2%.

TYPICAL CHARACTERISTICS  
MUN2112, MMUN2112L, MUN5112, DTA124EE, DTA124EM3

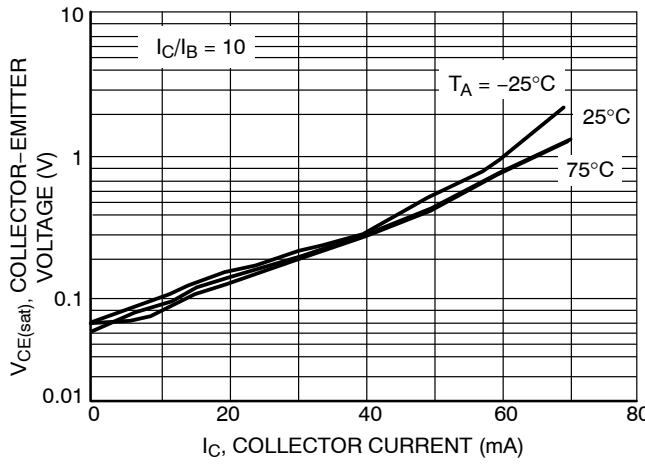


Figure 2.  $V_{CE(sat)}$  vs.  $I_C$

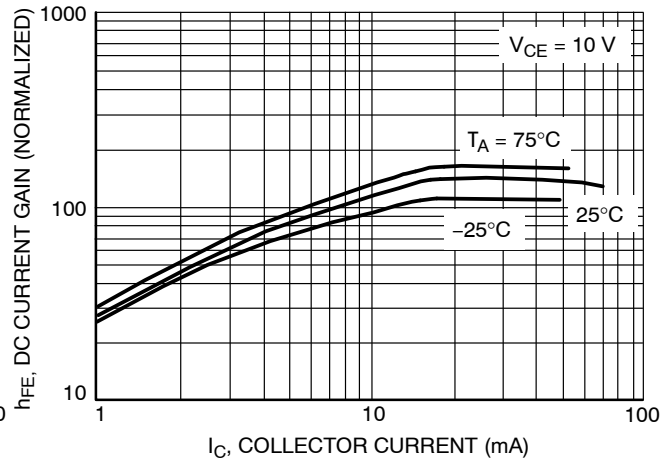


Figure 3. DC Current Gain

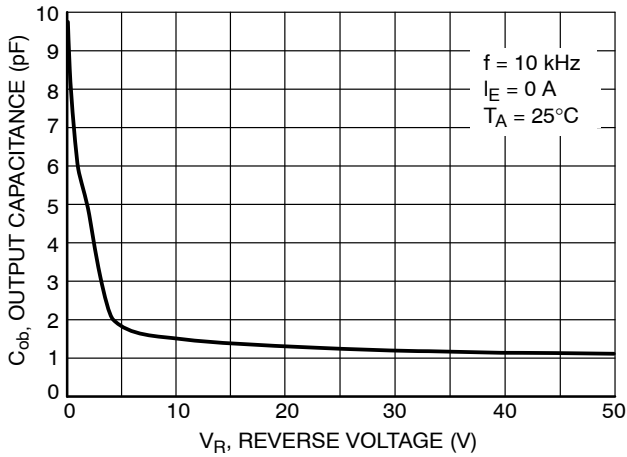


Figure 4. Output Capacitance

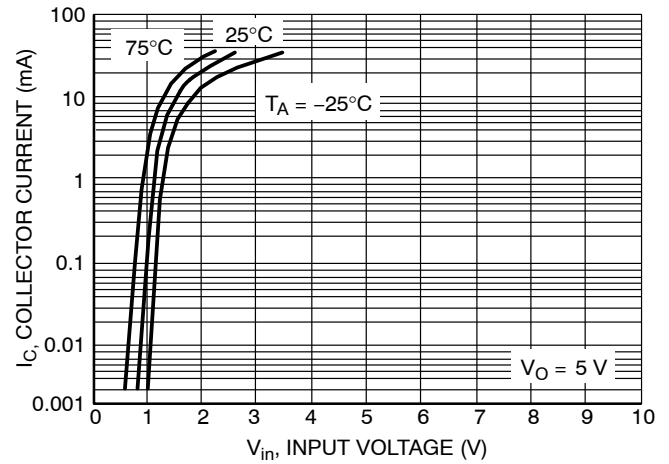


Figure 5. Output Current vs. Input Voltage

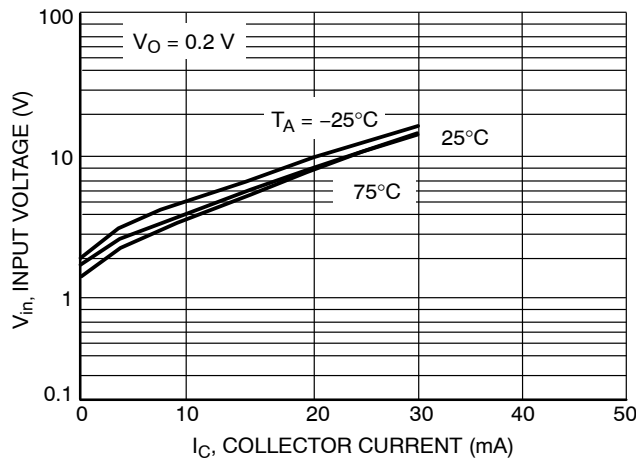


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – NSBA124EF3

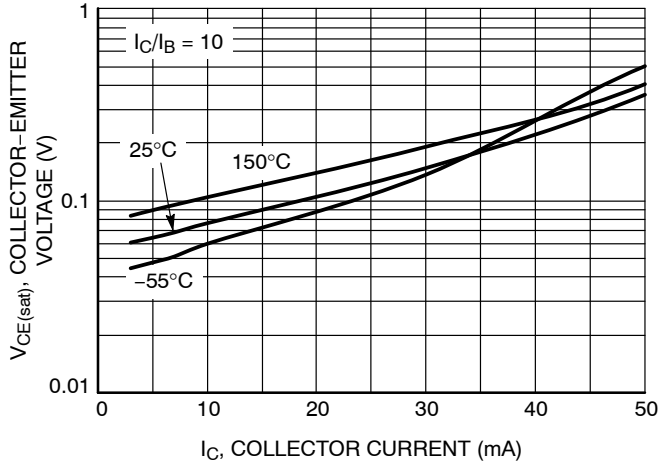


Figure 7.  $V_{CE(sat)}$  vs.  $I_C$

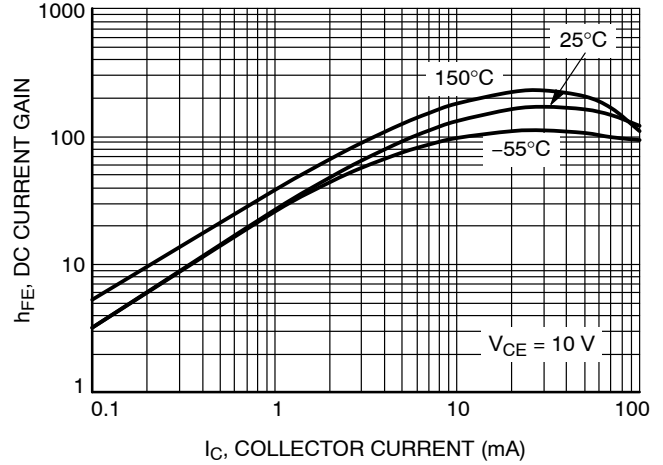


Figure 8. DC Current Gain

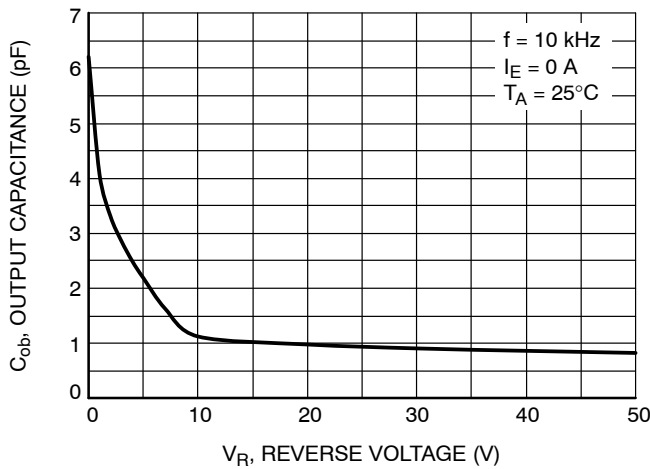


Figure 9. Output Capacitance

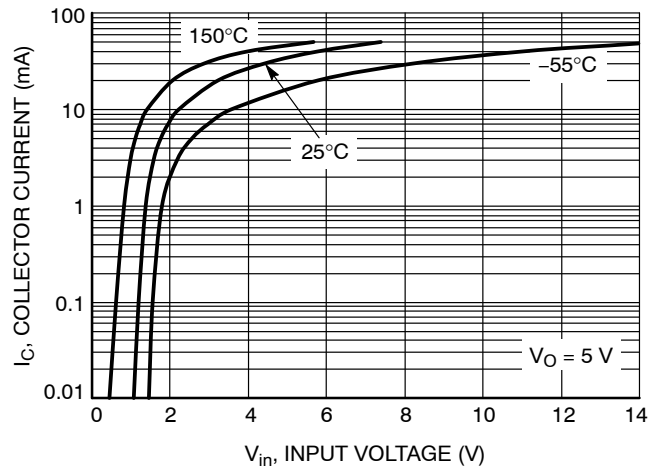


Figure 10. Output Current vs. Input Voltage

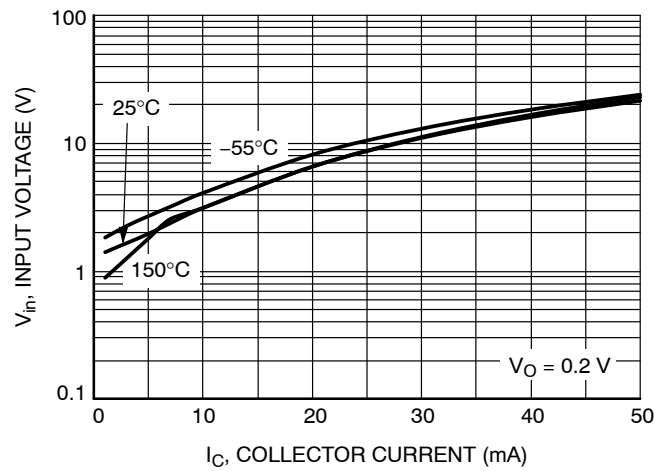
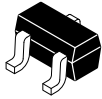


Figure 11. Input Voltage vs. Output Current

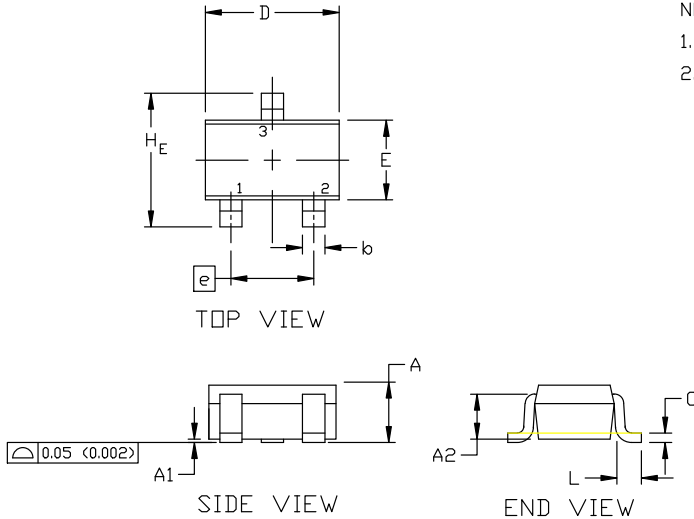
# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

## SC-70 (SOT-323) CASE 419 ISSUE R

DATE 11 OCT 2022

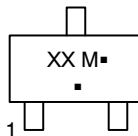


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

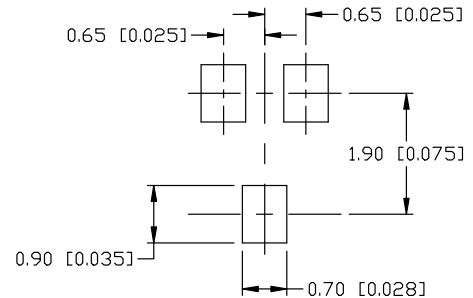
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H <sub>E</sub>	2.00	2.10	2.40	0.079	0.083	0.095

### GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

### SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE
STYLE 6: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 7: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE
				STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE

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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

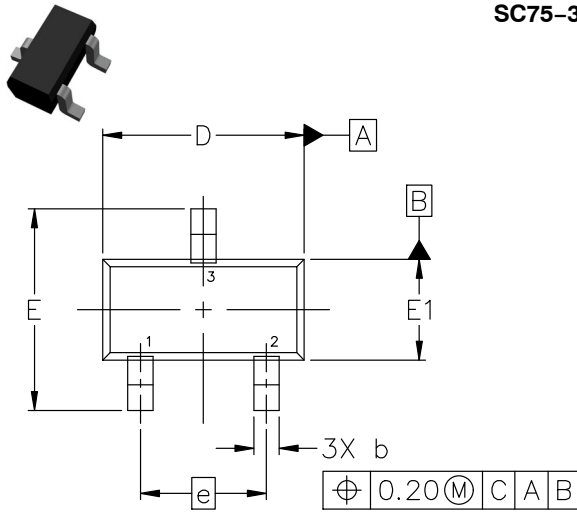
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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

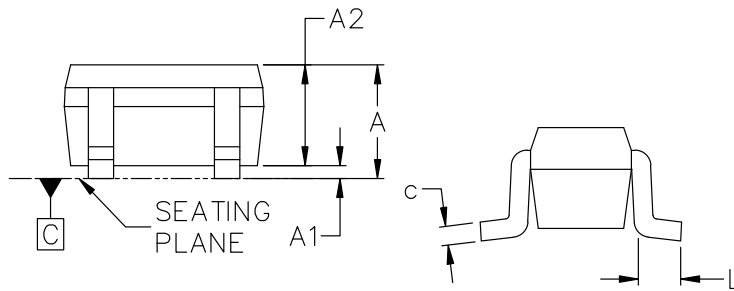


**SC75-3 1.60x0.80x0.80, 1.00P**  
CASE 463  
ISSUE H

DATE 01 FEB 2024



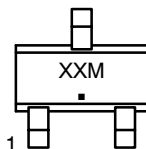
TOP VIEW



SIDE VIEW

END VIEW

**GENERIC MARKING DIAGRAM\***



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

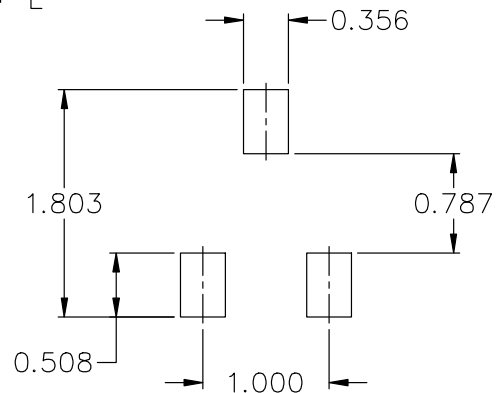
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR
- STYLE 2:  
PIN 1. ANODE  
2. N/C  
3. CATHODE
- STYLE 3:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE
- STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE
- STYLE 5:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	0.80 REF.		
b	0.15	0.20	0.30
c	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
e	1.00 BSC		
L	0.10	0.15	0.20



RECOMMENDED MOUNTING FOOTPRINT\*

\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

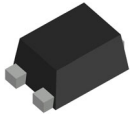
<b>DOCUMENT NUMBER:</b>	<b>98ASB15184C</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SC75-3 1.60x0.80x0.80, 1.00P</b>	<b>PAGE 1 OF 1</b>

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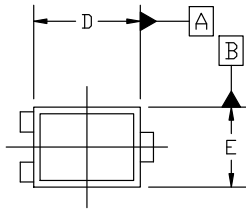
# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

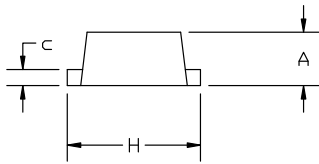


**SOT-1123 0.80x0.60x0.37, 0.35P**  
**CASE 524AA**  
**ISSUE D**

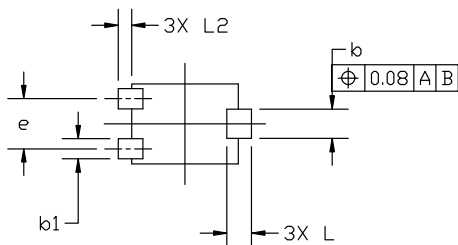
DATE 18 JAN 2024



TOP VIEW

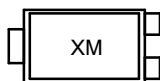


SIDE VIEW



BOTTOM VIEW

**GENERIC MARKING DIAGRAM\***



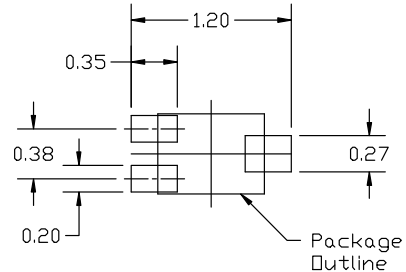
X = Specific Device Code  
M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.15	0.22	0.28
b1	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.75	0.80	0.85
E	0.55	0.60	0.65
e	0.35	0.38	0.40
H	0.950	1.000	1.050
L	0.185 REF		
L2	0.05	0.10	0.15



**RECOMMENDED MOUNTING FOOTPRINT**

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERM/D.

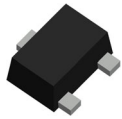
STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN
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<b>DESCRIPTION:</b>	<b>SOT-1123 0.80x0.60x0.37, 0.35P</b>	<b>PAGE 1 OF 1</b>

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS



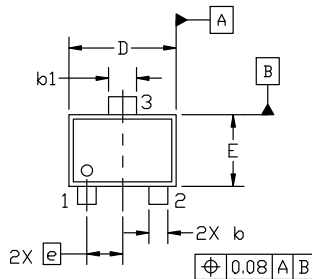
**SOT-723 1.20x0.80x0.50, 0.40P**  
**CASE 631AA**  
**ISSUE E**

DATE 24 JAN 2024

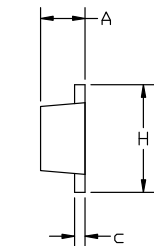
**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

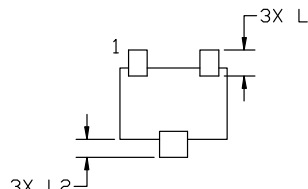
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



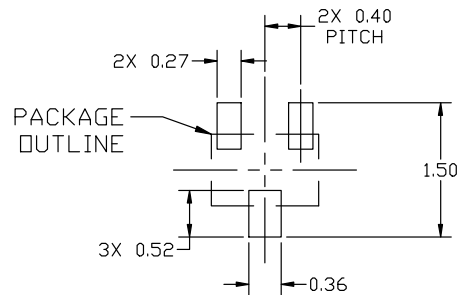
TOP VIEW



SIDE VIEW

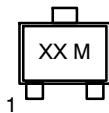


BOTTOM VIEW



RECOMMENDED MOUNTING FOOTPRINT

**GENERIC MARKING DIAGRAM\***



XX = Specific Device Code  
M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURCE
3. COLLECTOR	3. CATHODE	3. CATHODE	3. ANODE	3. DRAIN

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<b>DESCRIPTION:</b>	<b>SOT-723 1.20x0.80x0.50, 0.40P</b>	<b>PAGE 1 OF 1</b>

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